



N-Channel 20-V (D-S) MOSFET with Trench Schottky Diode

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
20	0.053 at $V_{GS} = 4.5$ V	4.5	4.1 nC
	0.063 at $V_{GS} = 2.5$ V	4.5	
	0.077 at $V_{GS} = 1.8$ V	4.5	

SCHOTTKY PRODUCT SUMMARY

V_{KA} (V)	V_f (V) Diode Forward Voltage	I_F (A) ^a
20	0.45 at 1 A	2

FEATURES

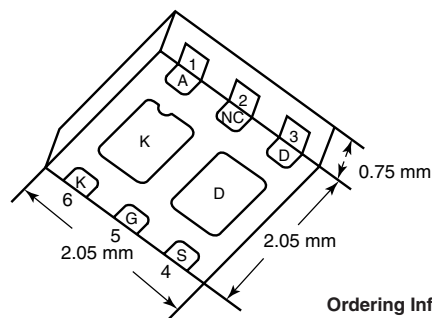
- Halogen-free
- LITTLE FOOT® Plus Schottky Power MOSFET
- New Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
 - Thin 0.75 mm profile
- Low V_f Trench Schottky Diode

RoHS
COMPLIANT

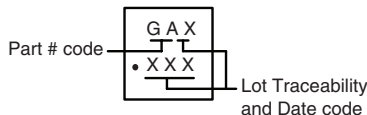
APPLICATIONS

- Load Switch for Portable Devices (MP3/Cellular)
- Boost Converter

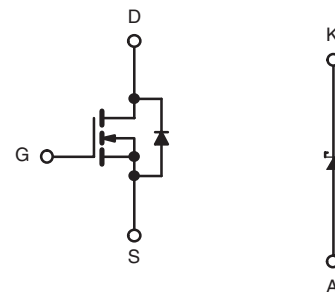
PowerPAK SC-70-6 Dual



Marking Code



Ordering Information: SiA810DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage (MOSFET)		V _{DS}	20	V	
Reverse Voltage (Schottky)		V _{KA}	20		
Gate-Source Voltage (MOSFET)		V _{GS}	± 8		
Continuous Drain Current (T _J = 150 °C) (MOSFET)	T _C = 25 °C	I _D	4.5 ^a	A	
	T _C = 70 °C		4.5 ^a		
	T _A = 25 °C		4.5 ^{a, b, c}		
	T _A = 70 °C		3.8 ^{b, c}		
Pulsed Drain Current (MOSFET)		I _{DM}	20		
Continuous Source-Drain Diode Current (MOSFET Diode Conduction)	T _C = 25 °C	I _S	4.5 ^a		
	T _A = 25 °C		1.6 ^{b, c}		
Average Forward Current (Schottky)		I _F	2 ^b		
Pulsed Forward Current (Schottky)		I _{FM}	5		
Maximum Power Dissipation (MOSFET)	T _C = 25 °C	P _D	6.5	W	
	T _C = 70 °C		5		
	T _A = 25 °C		1.9 ^{b, c}		
	T _A = 70 °C		1.2 ^{b, c}		
Maximum Power Dissipation (Schottky)	T _C = 25 °C		6.8		
	T _C = 70 °C		4.3		
	T _A = 25 °C		1.6 ^{b, c}		
	T _A = 70 °C		1.0 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^{d, e}			260		

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET) ^{b, f}	$t \leq 5$ s	R_{thJA}	52	65	°C/W
Maximum Junction-to-Case (Drain) (MOSFET)	Steady State	R_{thJC}	12.5	16	
Maximum Junction-to-Ambient (Schottky) ^{b, g}	$t \leq 5$ s	R_{thJA}	62	76	
Maximum Junction-to-Case (Drain) (Schottky)	Steady State	R_{thJC}	15	18.5	

Notes:

a. Package limited.

b. Surface Mounted on 1" x 1" FR4 board.

c. $t = 5$ s.d. See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under Steady State conditions is 110 °C/W.

g. Maximum under Steady State conditions is 110 °C/W.

SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$ V, $I_D = 250$ μ A	20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250$ μ A		1		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 2.8		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250$ μ A	0.4		1	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 8$ V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20$ V, $V_{GS} = 0$ V			1	μ A
		$V_{DS} = 20$ V, $V_{GS} = 0$ V, $T_J = 55$ °C			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq 5$ V, $V_{GS} = 4.5$ V	20			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 4.5$ V, $I_D = 3.7$ A		0.043	0.053	Ω
		$V_{GS} = 2.5$ V, $I_D = 3.4$ A		0.052	0.063	
		$V_{GS} = 1.8$ V, $I_D = 1.1$ A		0.062	0.077	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10$ V, $I_D = 3.7$ A		15		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 10$ V, $V_{GS} = 0$ V, $f = 1$ MHz		400		pF
Output Capacitance	C_{oss}			70		
Reverse Transfer Capacitance	C_{rss}			40		
Total Gate Charge	Q_g	$V_{DS} = 10$ V, $V_{GS} = 8$ V, $I_D = 4.8$ A		7	11.5	nC
Gate-Source Charge	Q_{gs}	$V_{DS} = 10$ V, $V_{GS} = 4.5$ V, $I_D = 4.8$ A		4.1	7	
Gate-Drain Charge	Q_{gd}			0.65		
Gate Resistance	R_g	$f = 1$ MHz		2.5		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10$ V, $R_L = 2.6$ Ω $I_D \cong 3.8$ A, $V_{GEN} = 4.5$ V, $R_g = 1$ Ω		5	10	ns
Rise Time	t_r			32	50	
Turn-Off Delay Time	$t_{d(off)}$			30	45	
Fall Time	t_f			53	80	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10$ V, $R_L = 2.6$ Ω $I_D \cong 3.8$ A, $V_{GEN} = 8$ V, $R_g = 1$ Ω		5	10	
Rise Time	t_r			12	20	
Turn-Off Delay Time	$t_{d(off)}$			15	25	
Fall Time	t_f			10	15	



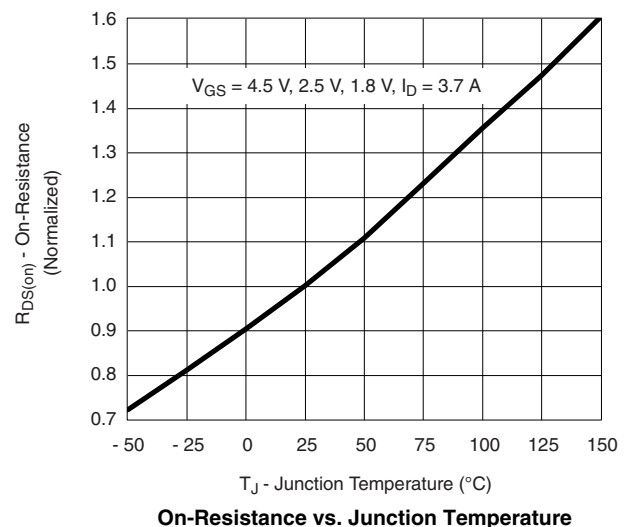
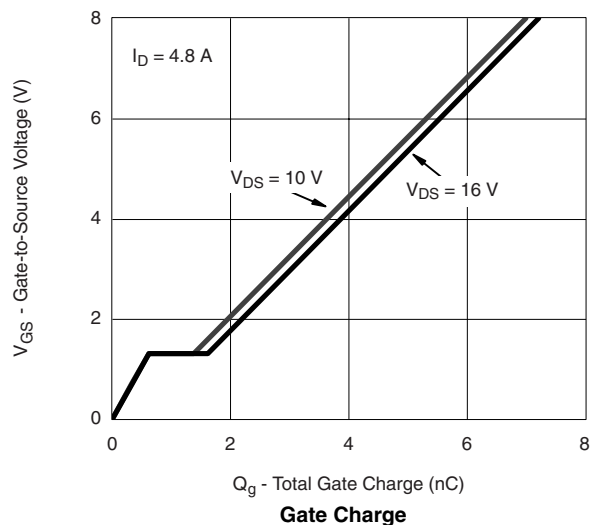
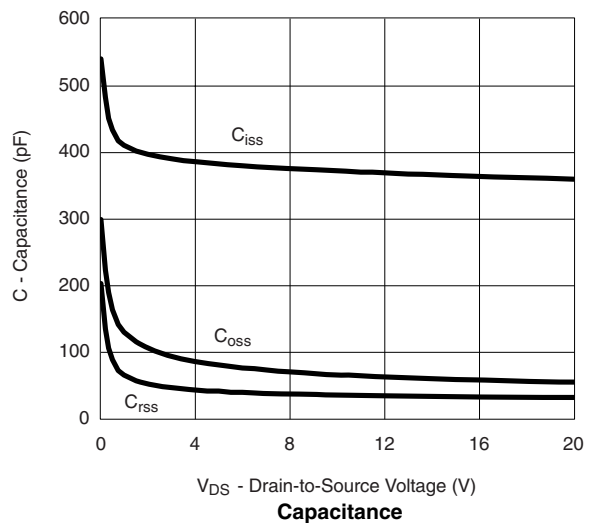
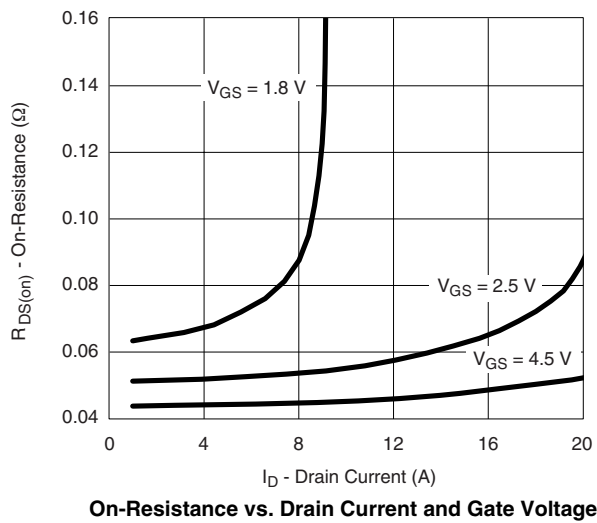
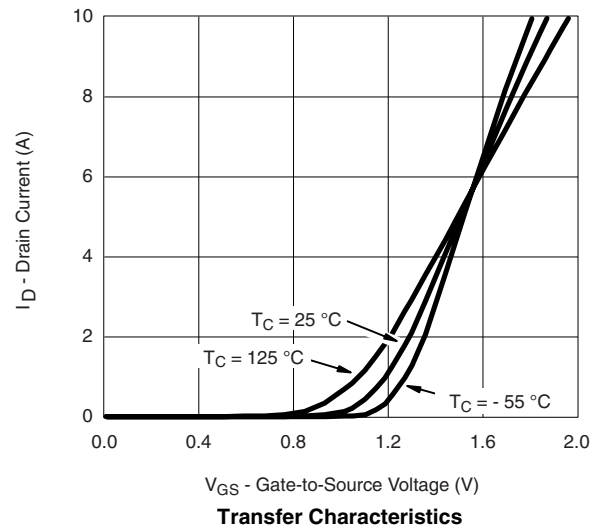
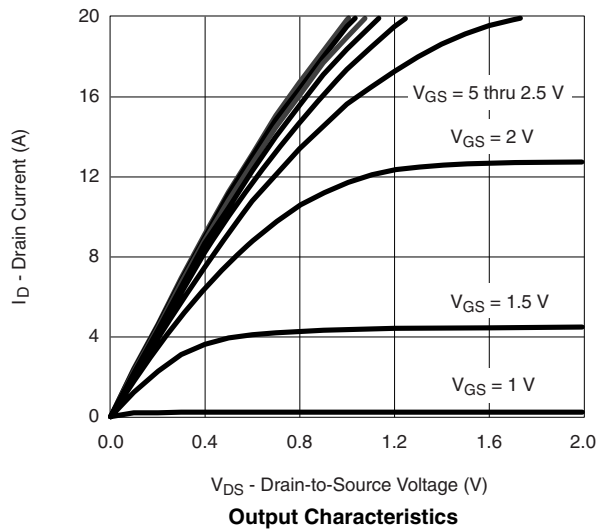
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^{\circ}\text{C}$			4.5	A
Pulse Diode Forward Current	I_{SM}				20	
Body Diode Voltage	V_{SD}	$I_S = 3.8\text{ A}$, $V_{GS} = 0\text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 3.8\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^{\circ}\text{C}$		15	30	ns
Body Diode Reverse Recovery Charge	Q_{rr}			8.5	20	nC
Reverse Recovery Fall Time	t_a			10		ns
Reverse Recovery Rise Time	t_b			5		

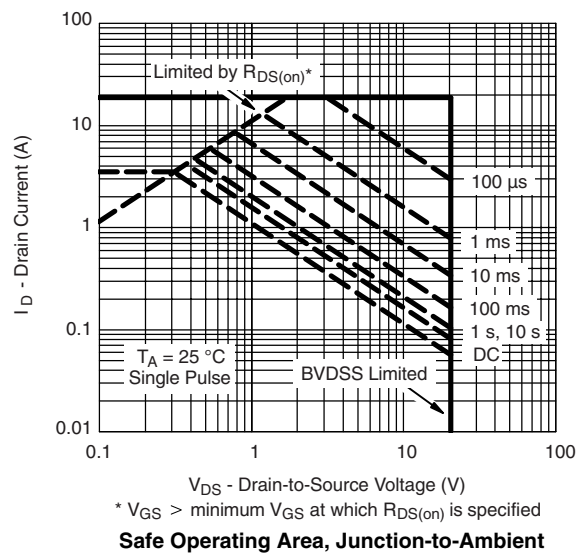
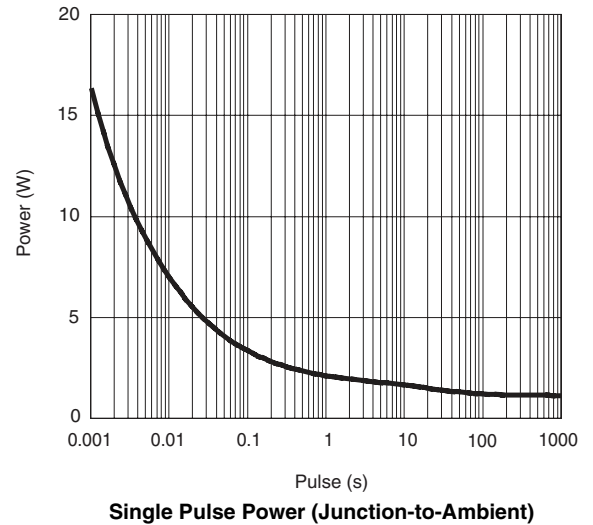
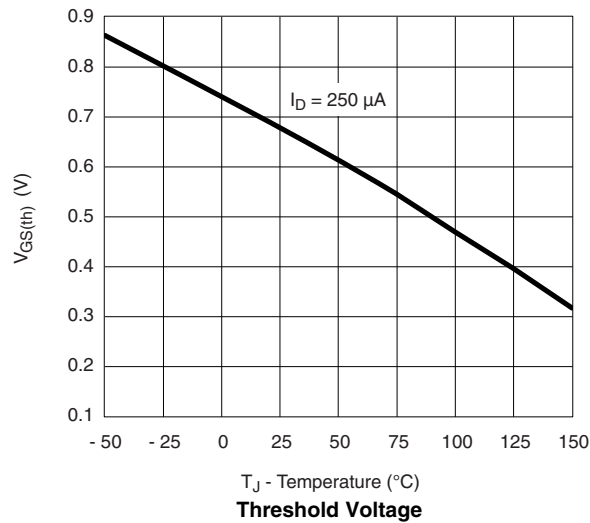
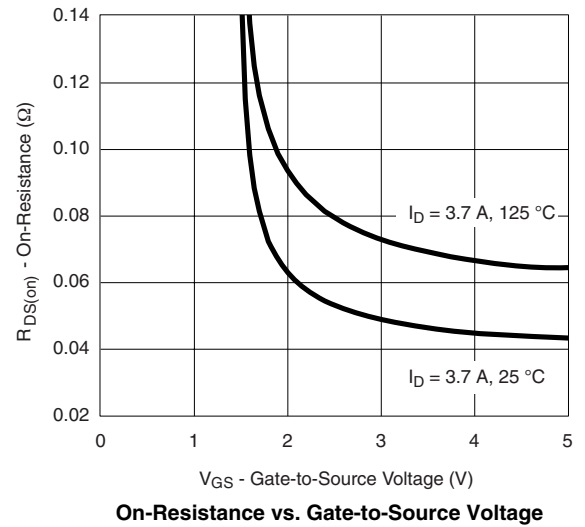
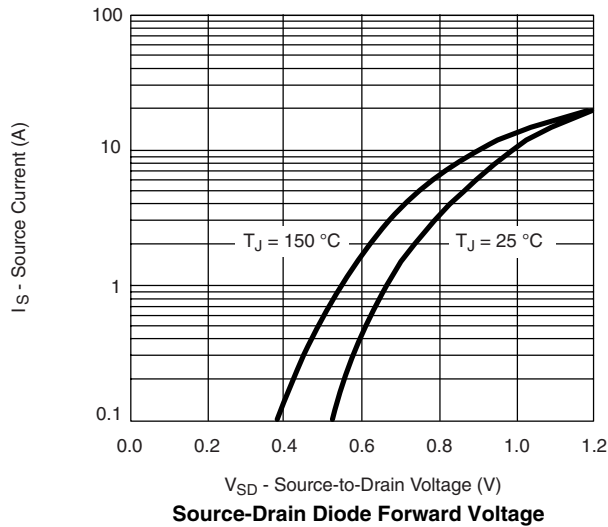
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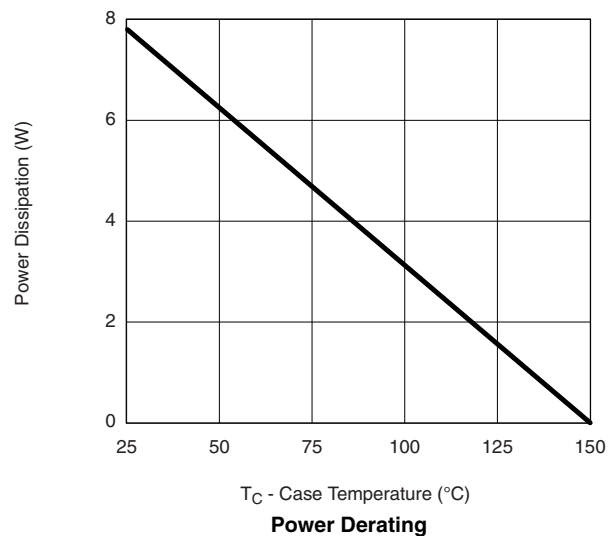
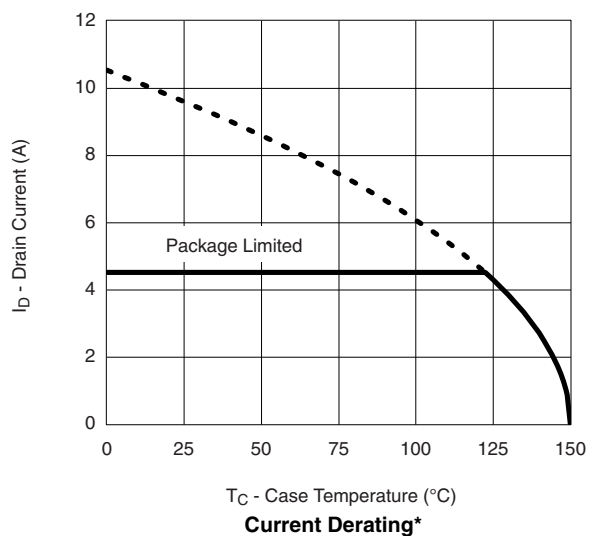
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

SCHOTTKY SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage Drop	V_F	$I_F = 1\text{ A}$		0.41	0.45	V
		$I_F = 1\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$		0.36	0.41	
Maximum Reverse Leakage Current	I_{rm}	$V_r = 5\text{ V}$		0.015	0.08	mA
		$V_r = 5\text{ V}$, $T_J = 85\text{ }^{\circ}\text{C}$		0.50	5.00	
		$V_r = 20\text{ V}$		0.02	0.10	
		$V_r = 20\text{ V}$, $T_J = 85\text{ }^{\circ}\text{C}$		0.7	7	
		$V_r = 20\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$		5	50	
Junction Capacitance	C_T	$V_r = 10\text{ V}$		60		pF

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

MOSFET TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted


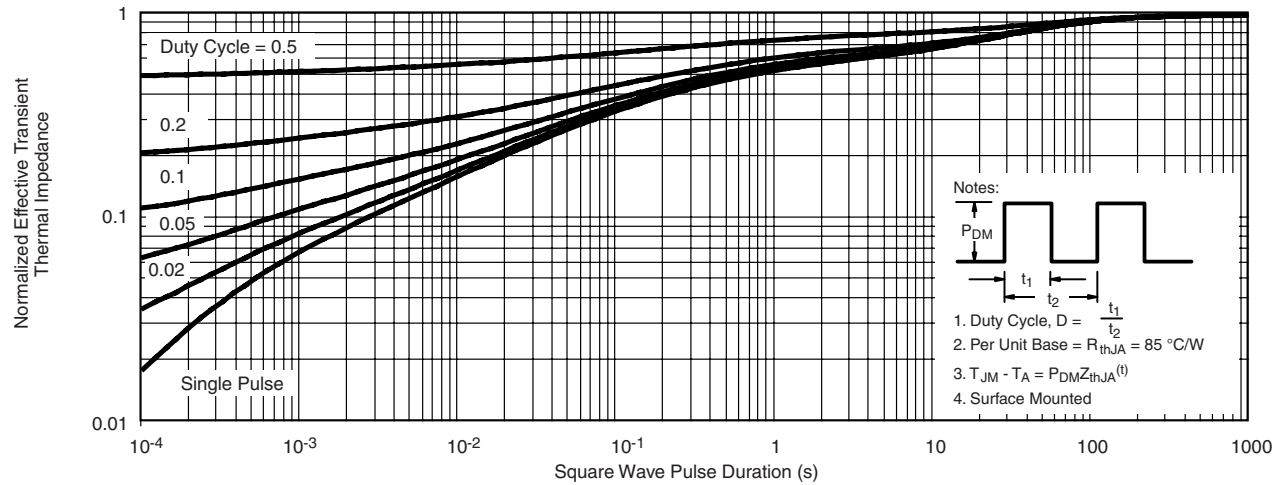
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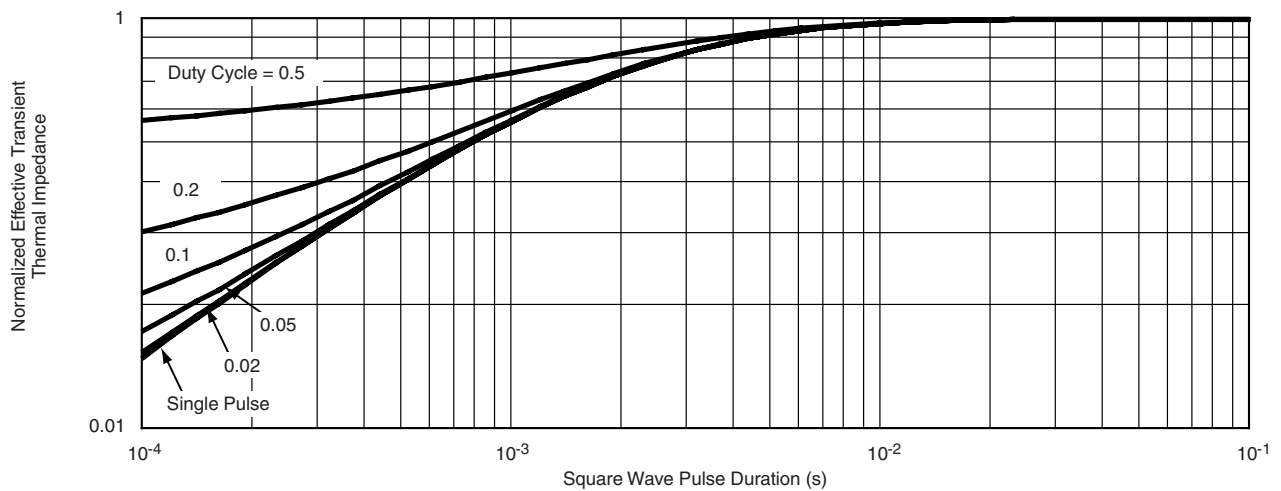
* The power dissipation P_D is based on $T_{J(max)} = 150\text{ }^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



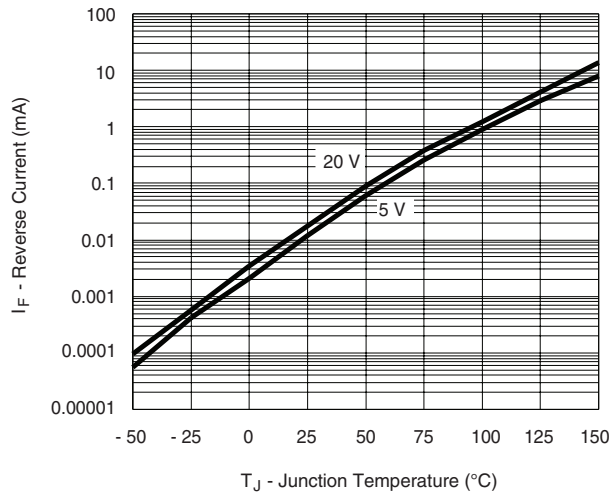
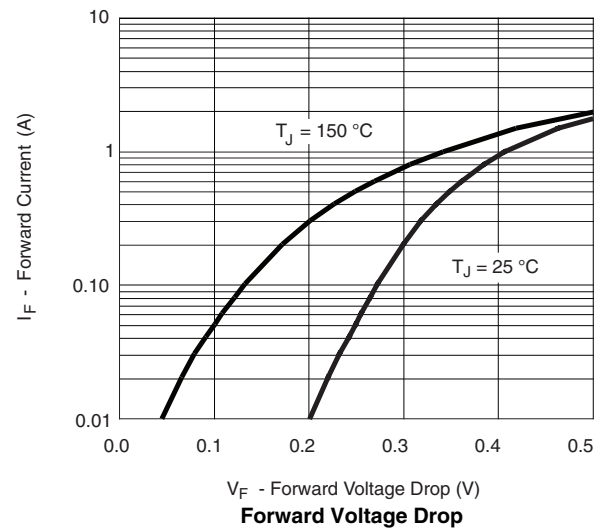
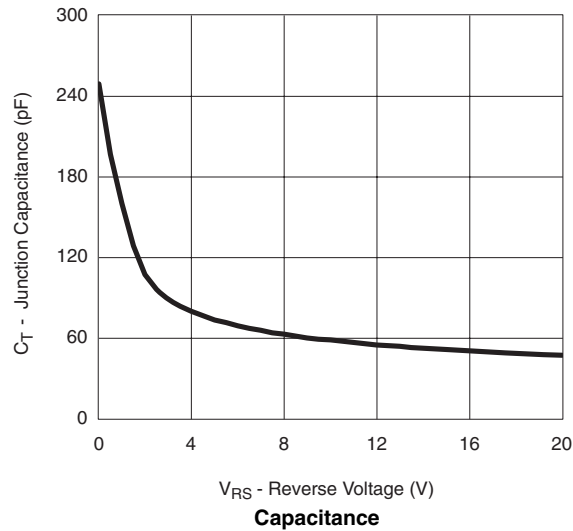
MOSFET TYPICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$, unless otherwise noted

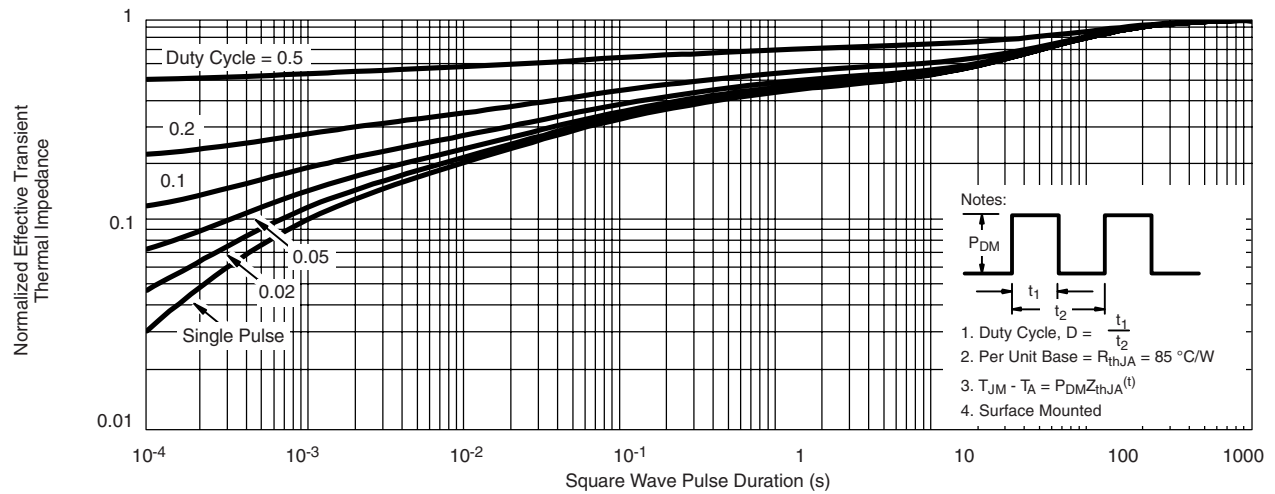


Normalized Thermal Transient Impedance, Junction-to-Ambient

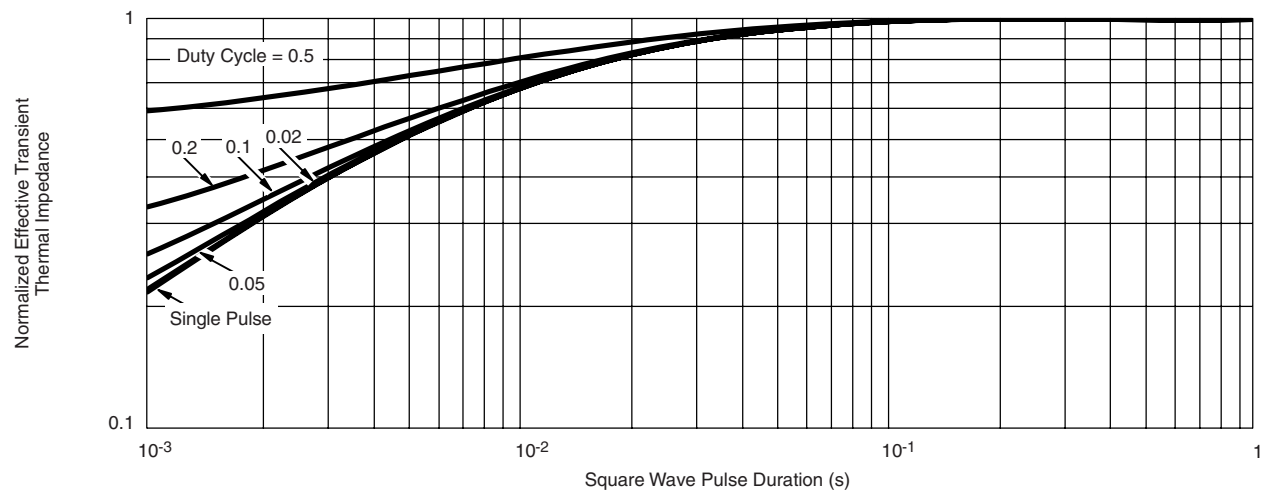


Normalized Thermal Transient Impedance, Junction-to-Case

SCHOTTKY TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Reverse Current vs. Junction Temperature

Forward Voltage Drop

Capacitance

**SCHOTTKY TYPICAL CHARACTERISTICS** $T_A = 25^\circ\text{C}$, unless otherwise noted

Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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